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FGA50S110P 1100 V, 50 A Shorted-anode IGBT

March 2016

Features

- · Intrinsic Anti-parallel Diode for Soft-switching Applications
- · High Switching Frequency Range 10 kHz to 50kHz
- High Temperature Stable Behavior (T_{jmax} = 175°C)
- Low Saturation Voltage Drop : VcE(sat) = 2.06 V @ Ic = 50 A
- · Robust Pot Detection Noise Immunity
- · RoHS Compliant (Pb-free lead plating)

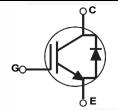
Applications

- · Induction Cooker, Rice-jar, and Microwave Oven
- · Soft-switching Applications

General Description

Using advanced field stop trench and shorted-anode technology, Fairchild's shorted-anode trench IGBTs offer superior conduction and switching performances for switching applications. This device is tailored to induction cooker and microwave oven.





Absolute Maximum Ratings

Symbol	Description		Ratings	Unit	
V _{CES}	Collector to Emitter Voltage		1100	V	
V _{GES}	Gate to Emitter Voltage		± 25	V	
I _C	Collector Current	@ T _C = 25°C	50	A	
.0	Collector Current	@ T _C = 100°C	30	A	
I _{CM (1)}	Pulsed Collector Current		120	A	
I _F	Diode Continuous Forward Current	@ T _C = 25°C	50	A	
'F	Diode Continuous Forward Current	@ T _C = 100°C	30	A	
P _D	Maximum Power Dissipation	@ T _C = 25°C	300	W	
. 0	Maximum Power Dissipation	@ T _C = 100°C	150	W	
T _J	Operating Junction Temperature		-55 to +175	°C	
T _{stg}	Storage Temperature Range		-55 to +175	°C	
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	6	300	°C	

Thermal Characteristics

Symbol Parameter		Тур.	Max.	Unit	
$R_{\theta JC}(IGBT)$	H _{BJC} (IGBT) Thermal Resistance, Junction to Case, Max		0.5	°C/W	
R _{0JA} Thermal Resistance, Junction to Ambient, Max		-	40	°C/W	

Notes:

1: Limited by T_{jmax}

Package Marking and Ordering Information

De	Device Marking	Device	Package	Reel Size	Tape Width	Quantity	
	FGA50S110P	FGA50S110P	TO-3PN	-	-	30	

Electrical Characteristics of the IGBT $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
I _{CES}	Collector Cut-Off Current	V _{CE} = 1100 V, V _{GE} = 0 V	-	-	1	mA
I _{GES}	G-E Leakage Current	V _{GE} = V _{GES} , V _{CE} = 0 V	-	-	±500	nA
On Charac	teristics					
V _{GE(th)}	G-E Threshold Voltage	I_C = 50 mA, V_{CE} = V_{GE}	4.5	5.6	7.5	V
(*)	Collector to Emitter Saturation Voltage	I _C = 50 A, V _{GE} = 15 V T _C = 25°C	-	2.06	2.6	V
V _{CE(sat)}		I _C = 50 A, V _{GE} = 15 V T _C = 125°C	-	2.54	-	V
		I _C = 50 A, V _{GE} = 15 V, T _C = 175°C	-	2.7	-	V
	Diode Forward Voltage	I _F = 50 A, T _C = 25°C	-	1.96	2.6	V
V_{FM}		I _F = 50 A, T _C = 175°C	-	2.67	-	V
Dynamic C	haracteristics		•			
C _{ies}	Input Capacitance		-	2056	-	pF
C _{oes}	Output Capacitance	$V_{CE} = 30 \text{ V}, V_{GE} = 0 \text{ V},$ f = 1 MHz	-	47.8	-	pF
C _{res}	Reverse Transfer Capacitance	1 - 1 1/1/12	-	35.8	-	pF
	Characteristics					
t _{d(on)}	Turn-On Delay Time	-	-	24	-	ns
t _r	Rise Time		-	294	-	ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 600 \text{ V}, I_{C} = 50 \text{ A},$	-	280	-	ns
t _f	Fall Time	$R_G = 10 \Omega V_{GE} = 15 V$, Resistive Load, $T_C = 25^{\circ}C$	-	95	-	ns
E _{on}	Turn-On Switching Loss		-	2240	-	uJ
E _{off}	Turn-Off Switching Loss		-	990	-	uJ
E _{ts}	Total Switching Loss		-	3230	-	uJ
t _{d(on)}	Turn-On Delay Time		-	24	-	ns
t _r	Rise Time		-	346	-	ns
$t_{d(off)}$	Turn-Off Delay Time	$V_{CC} = 600 \text{ V}, I_{C} = 50 \text{ A},$ $R_{G} = 10 \Omega, V_{GE} = 15 \text{ V},$ Resistive Load,, $T_{C} = 175^{\circ}\text{C}$	-	308	-	ns
t _f	Fall Time		-	184	-	ns
E _{on}	Turn-On Switching Loss		-	2640	-	uJ
E _{off}	Turn-Off Switching Loss		-	1820	-	uJ
E _{ts}	Total Switching Loss		-	4460	-	uJ
Qg	Total Gate Charge		-	195	-	nC
Q _{ge}	Gate to Emitter Charge	$V_{CE} = 600 \text{ V, } I_{C} = 50 \text{ A,}$ $V_{GE} = 15 \text{ V}$	-	15.4	-	nC
Q _{gc}	Gate to Collector Charge		-	99.9	_	nC

Figure 1. Typical Output Characteristics

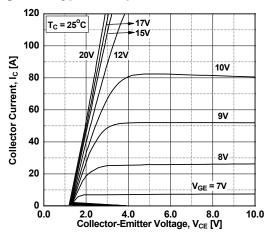


Figure 3. Typical Saturation Voltage Characteristics

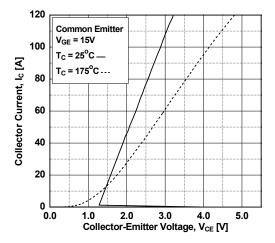


Figure 5. Saturation Voltage vs. Case
Temperature at Variant Current Level

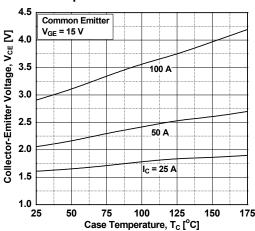


Figure 2. Typical Output Characteristics

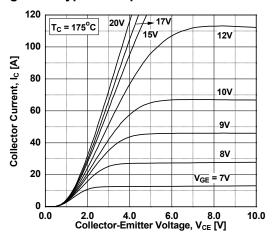


Figure 4. Transfer Characteristics

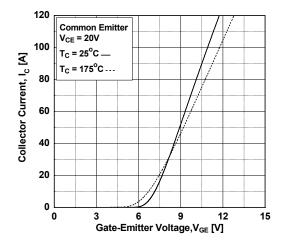


Figure 6. Saturation Voltage vs. V_{GE}

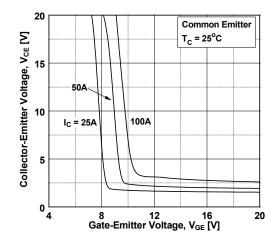


Figure 7. Saturation Voltage vs. V_{GE}

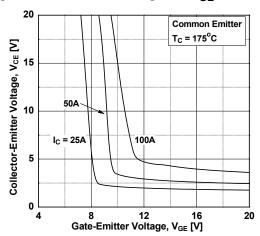


Figure 9. Gate charge Characteristics

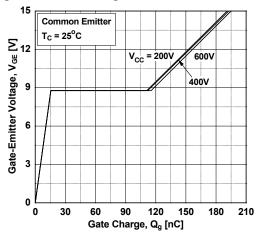


Figure 11. Turn-on Characteristics vs.
Gate Resistance

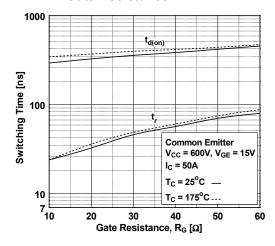


Figure 8. Capacitance Characteristics

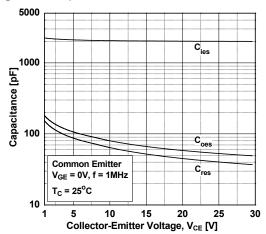


Figure 10. SOA Characteristics

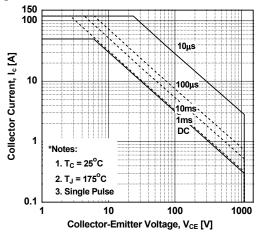


Figure 12. Turn-off Characteristics vs.
Gate Resistance

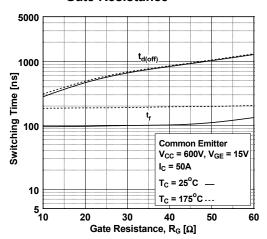
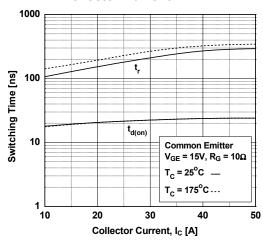


Figure 13. Turn-on Characteristics vs. Collector Current



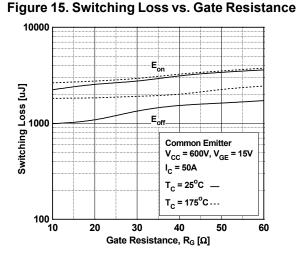


Figure 17. Turn off Switching SOA Characteristics

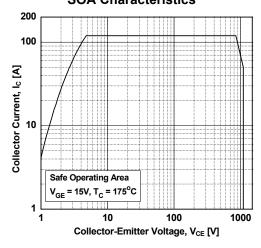


Figure 14. Turn-off Characteristics vs.
Collector Current

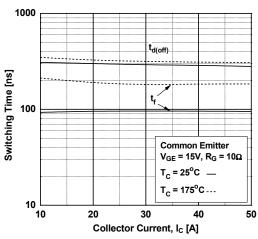


Figure 16. Switching Loss vs. Collector Current

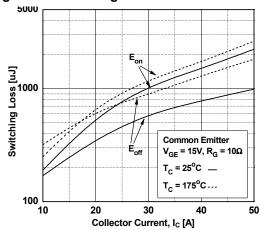


Figure 18. Forward Characteristics

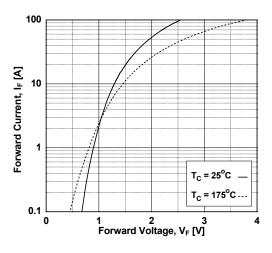
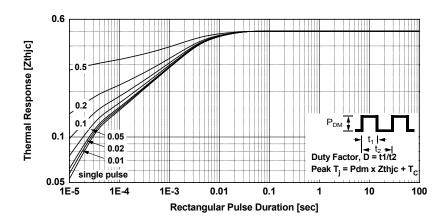
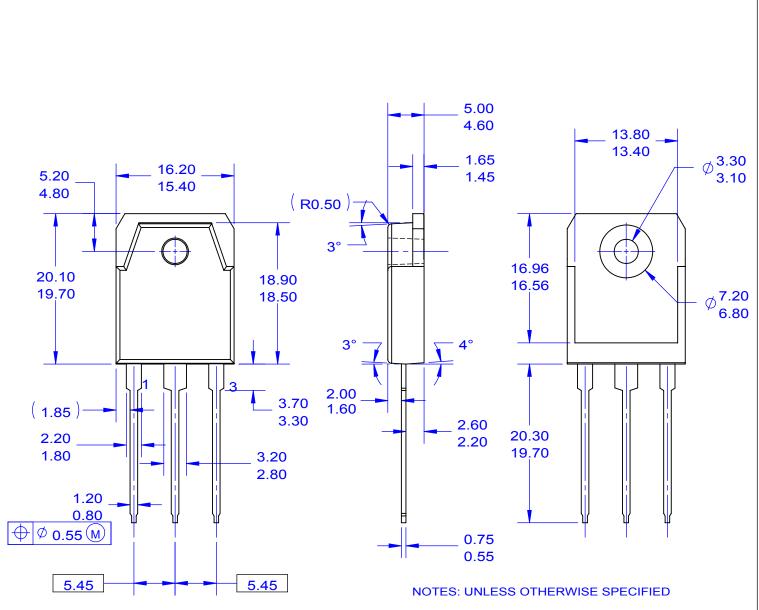
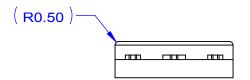


Figure 19. Transient Thermal Impedance of IGBT







- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSION AND TOLERANCING PER ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS.
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